

P-Channel 20 V (D-S) MOSFET

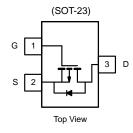
PRODUCT SUMMARY				
V _{DS} (V)	- 20			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.070			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -2.5 V$	0.093			
I _D (A)	- 5.0			
Configuration	Single			

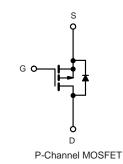
FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- AEC-Q101 Qualified^d
- + 100 % $\rm R_g$ and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



COMPLIANT HALOGEN





ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted	(b	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	- 20	V
Gate-Source Voltage		V _{GS}	± 8	
Continuous Drain Current	T _C = 25 °C		- 5.0	
	T _C = 125 °C	l _D	- 3.2	
Continuous Source Current (Diode Conduction) ^a		I _S	- 3	А
Pulsed Drain Current ^b		I _{DM}	- 15	
Single Pulse Avalanche Current		I _{AS}	- 3	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	4	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	P	3	10/
	T _C = 125 °C	P _D	1	W
Operating Junction and Storage Temperature Range		TJ, Tsta	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	166	°C/W		
Junction-to-Foot (Drain)		R _{thJF}	50	0/10		

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

DTS2301S

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = -250 \ \mu A$		- 20	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$		-	- 1.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$		-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V _{DS} = - 20 V	-	-	- 1		
	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = - 20 V, T_{J} = 125 °C	-	-	- 50	μA	
		$V_{GS} = 0 V$	V_{DS} = - 20 V, T_{J} = 175 °C	-	-	- 150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 4.5 V	$V_{DS} \ge 5 V$	- 5	-	-	Α	
	P	V _{GS} = - 4.5 V	I _D = - 2.8 A	-	0.070	0.077		
Drain-Source On-State Resistance ^a	Resistance ^a $R_{DS(on)}$ $V_{GS} = -2.5 V$ $I_D = -2 A$	I _D = - 2 A	-	0.093	0.105	Ω		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 1.6 V, I _D = - 2.8 A		-	7	-	S	
Dynamic ^b	-							
Input Capacitance	C _{iss}		V _{DS} = - 10 V, f = 1 MHz	-	340	425	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	80	100		
Reverse Transfer Capacitance	C _{rss}			-	55	70		
Total Gate Charge ^c	Qg			-	5	8		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 4.5 V	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -2.8 \text{ A}$	-	0.7	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	1.3	-		
Gate Resistance	R _g	f = 1 MHz		5.5	10	14.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}				15	22	ns	
Rise Time ^c	t _r	V_{DD} = - 10 V, R _L = 10 Ω I _D \cong - 1 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		-	14	21		
Turn-Off Delay Time ^c	t _{d(off)}			-	30	45		
Fall Time ^c	t _f			-	9	15		
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed Current ^a	I _{SM}			-		- 5.0	Α	
Forward Voltage	V _{SD}	I _F = - 1.6 A, V _{GS} = 0		-	- 0.8	- 1.2	V	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

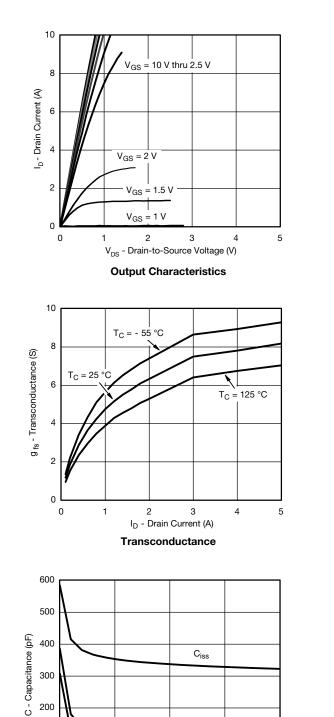
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Coss

5

10

Capacitance

V_{DS} - Drain-to-Source Voltage (V)

15

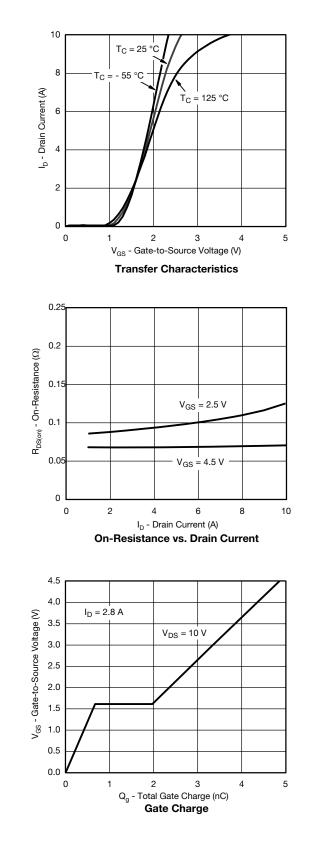
20

 $\mathsf{C}_{\mathsf{rss}}$

100

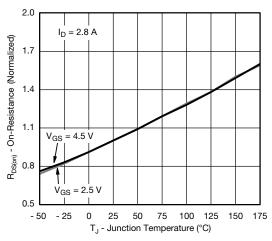
0

0

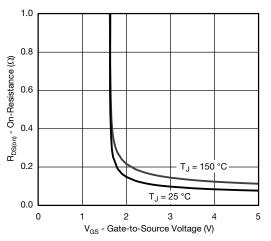




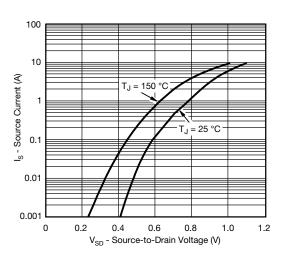
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



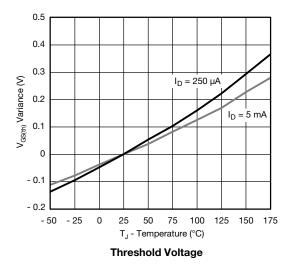
On-Resistance vs. Junction Temperature

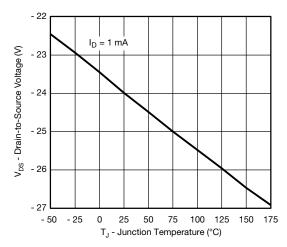


On-Resistance vs. Gate-to-Source Voltage



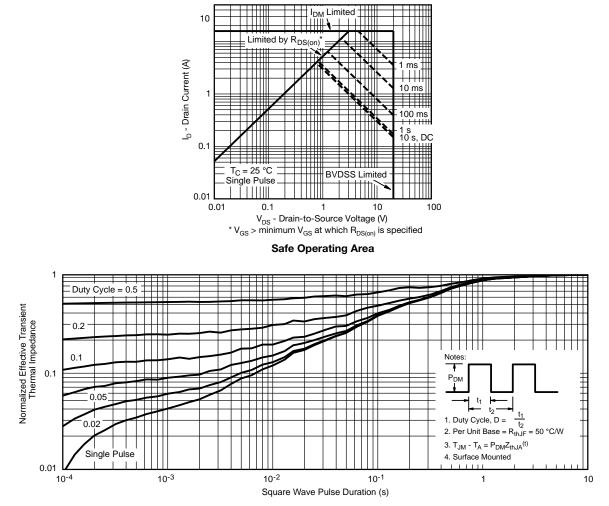
Source-Drain Diode Forward Voltage





Drain Source Breakdown vs. Junction Temperature

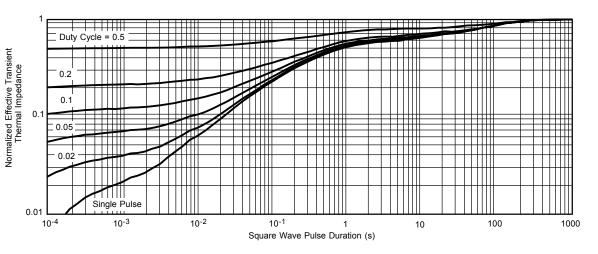
THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

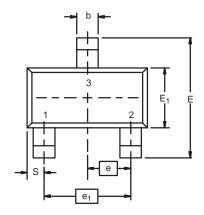
- Normalized Transient Thermal Impedance Junction-to-Foot (25 C)

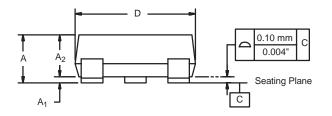
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

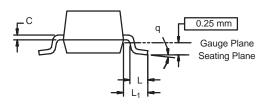
[•] The characteristics shown in the two graphs



SOT-23 : 3-LEAD



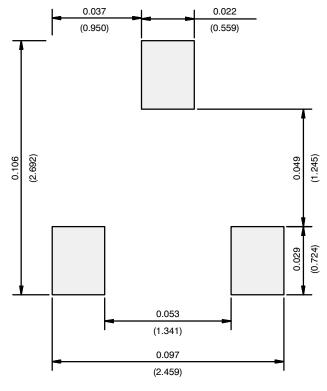




Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
А	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
C	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01				



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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